

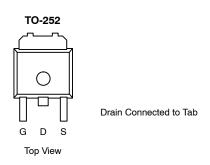
D452AL-VB Datasheet

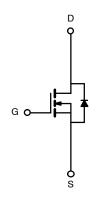
N-Channel 20-V (D-S)175 $^{\circ}$ C MOSFET

| PRODUCT SUMMARY | | | | | |
|---------------------|----------------------------------|---------------------------------|--|--|--|
| V _{DS} (V) | $r_{DS(on)}\left(\Omega\right)$ | I _D (A) ^a | | | |
| 20 | 0.0045 @ V _{GS} = 4.5 V | 100 | | | |
| | 0.006 @ V _{GS} = 2.5 V | 90 | | | |

FEATURES

- Trench Power MOSFET
- 175°C Maximum Junction Temperature
- 100% R_g Tested





N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED) | | | | | | |
|---|------------------------|-----------------------------------|---------------------|------|--|--|
| Parameter | | Symbol | Limit | Unit | | |
| Drain-Source Voltage | | V _{DS} | 20 | ., | | |
| Gate-Source Voltage | | V _{GS} | ±15 | | | |
| 0 " 0 " | T _C = 25°C | | 100 | | | |
| Continuous Drain Current ^a | T _C = 100°C | - I _D - | 80 | | | |
| Pulsed Drain Current | | I _{DM} | 200 | Α | | |
| Continuous Source Current (Diode Conduction) ^a | | IS | 65 | | | |
| M | T _C = 25°C | | 71 | 14/ | | |
| Maximum Power Dissipation | T _A = 25°C | P _D | 8.3 ^{b, c} | W | | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | -55 to 175 | °C | | |

| THERMAL RESISTANCE RATINGS | | | | | | | |
|--|--------------|-------------------|---------|---------|------|--|--|
| Parameter | | Symbol | Typical | Maximum | Unit | | |
| | t ≤ 10 sec. | R _{thJA} | 15 | 18 | °C/W | | |
| Maximum Junction-to-Ambient ^b | Steady State | | 40 | 50 | | | |
| Maximum Junction-to-Case | | R _{thJC} | 1.75 | 2.1 | | | |

Notes

- a. Package Limited
- b. Surface Mounted on 1" x 1" FR4 Board
- $c. \quad t \leq 10 \ \text{sec}$

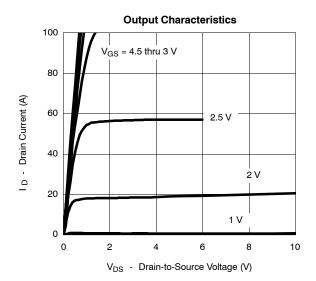


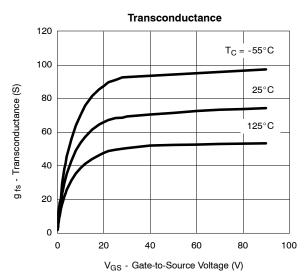
| Parameter | Symbol | Test Condition | Min | Typ ^a | Max | Unit |
|-------------------------------------|----------------------|---|--------|------------------|------|------|
| Static | . | | 1 | ı | | |
| Drain-Source Breakdown Voltage | V _{(BR)DSS} | V_{GS} = 0 V, I_D = 250 μA | 20 | | | V |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_D = 250 \mu A$ | 0.5 | | 1.5 | \ \ |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$ | | | ±100 | nA |
| | _ | V _{DS} = 20 V, V _{GS} = 0 V | | | 1 | |
| Zero Gate Voltage Drain Current | DSS | $V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$ | | | 50 | - μΑ |
| On-State Drain Current ^b | I _{D(on)} | $V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$ | 100 | | | Α |
| | | $V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$ | 20 A C | | I | Ω |
| Drain-Source On-State Resistanceb | r _{DS(on)} | V _{GS} = 4.5 V, I _D = 20 A, T _J = 125°C | | 0.0055 | | |
| | \ / | $V_{GS} = 2.5 \text{ V}, I_D = 20 \text{ A}$ | | 0.006 | | 1 |
| Forward Transconductanceb | 9 _{fs} | $V_{DS} = 5 \text{ V}, I_{D} = 40 \text{ A}$ | 20 | | | S |
| Dynamic ^a | | | • | | | |
| Input Capacitance | C _{iss} | | | 3660 | | pF |
| Output Capacitance | C _{oss} | $V_{GS} = 0 \text{ V}, V_{DS} = 20 \text{ V}, f = 1 \text{ MHz}$ | | 730 | | |
| Reverse Transfer Capacitance | C _{rss} | | | 375 | | |
| Total Gate Charge ^c | Qg | | | 26 | 35 | |
| Gate-Source Charge ^c | Q _{gs} | V_{DS} = 10 V, V_{GS} = 4.5 V, I_{D} = 40 A | | 5 | | nC |
| Gate-Drain Charge ^c | Q _{gd} | | | 7 | | |
| Gate Resistance | R _g | | 1 | | 3.7 | Ω |
| Turn-On Delay Time ^c | t _{d(on)} | | | 20 | 35 | |
| Rise Time ^c | t _r | V_{DD} = 10 V, R_L = 0.25 Ω | | 120 | 190 | |
| Turn-Off Delay Time ^c | t _{d(off)} | V_{DD} = 10 V, R_L = 0.25 Ω $I_D \cong$ 40 A, V_{GEN} = 4.5 V, R_G = 2.5 Ω | | 45 | 70 | ns |
| Fall Time ^c | t _f | | | 20 | 35 | |
| Source-Drain Diode Ratings an | d Characteristi | c (T _C = 25°C) | | | | |
| Pulsed Current | I _{SM} | | | | 100 | А |
| Diode Forward Voltage ^b | V _{SD} | I _F = 100 A, V _{GS} = 0 V | | 1.2 | 1.5 | V |
| Source-Drain Reverse Recovery Time | t _{rr} | I _F = 40 A, di/dt = 100 A/μs | | 35 | 70 | ns |

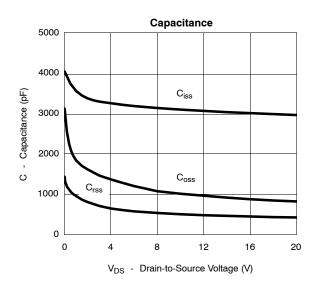
- Notes a. Guaranteed by design, not subject to production testing. b. Pulse test; pulse width $\leq 300~\mu s$, duty cycle $\leq 2\%$. c. Independent of operating temperature.

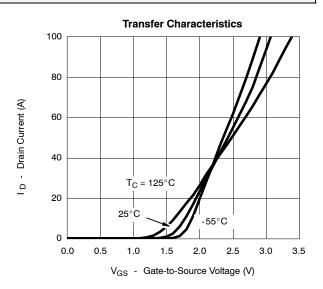


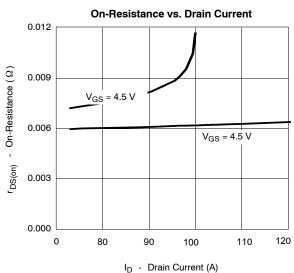
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

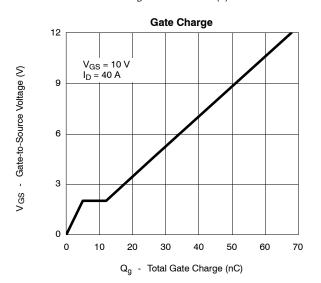






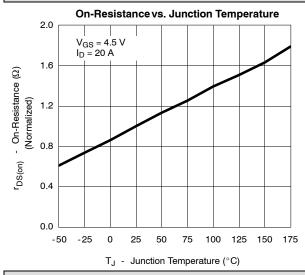


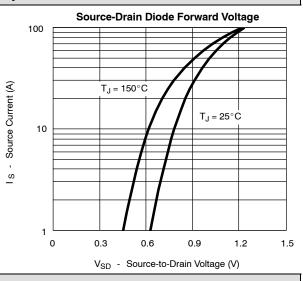




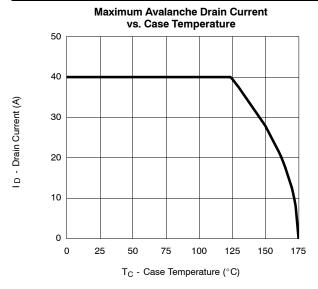


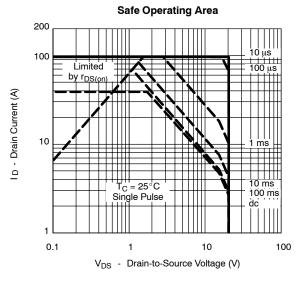
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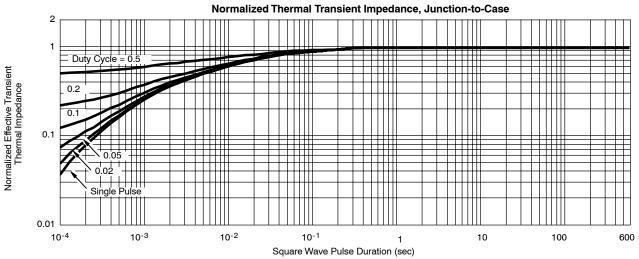




THERMAL RATINGS

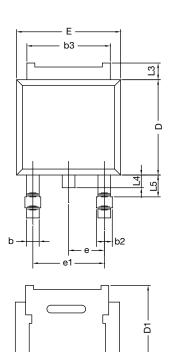


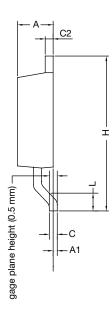






TO-252AA CASE OUTLINE





| | MILLIMETERS | | INCHES | | |
|--|-------------|-------|-----------|-------|--|
| DIM. | MIN. | MAX. | MIN. | MAX. | |
| Α | 2.18 | 2.38 | 0.086 | 0.094 | |
| A1 | - | 0.127 | - | 0.005 | |
| b | 0.64 | 0.88 | 0.025 | 0.035 | |
| b2 | 0.76 | 1.14 | 0.030 | 0.045 | |
| b3 | 4.95 | 5.46 | 0.195 | 0.215 | |
| С | 0.46 | 0.61 | 0.018 | 0.024 | |
| C2 | 0.46 | 0.89 | 0.018 | 0.035 | |
| D | 5.97 | 6.22 | 0.235 | 0.245 | |
| D1 | 5.21 | = | 0.205 | - | |
| Е | 6.35 | 6.73 | 0.250 | 0.265 | |
| E1 | 4.32 | = | 0.170 | - | |
| Н | 9.40 | 10.41 | 0.370 | 0.410 | |
| е | 2.28 BSC | | 0.090 BSC | | |
| e1 | 4.56 BSC | | 0.180 BSC | | |
| L | 1.40 | 1.78 | 0.055 | 0.070 | |
| L3 | 0.89 | 1.27 | 0.035 | 0.050 | |
| L4 | - | 1.02 | - | 0.040 | |
| L5 | 1.14 | 1.52 | 0.045 | 0.060 | |
| ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347 | | | | | |

Note

• Dimension L3 is for reference only.

服务热线:400-655-8788

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